TOSHIBA Field Effect Transistor Silicon P Channel MOS Type (U-MOSVI)

# **TPC8126**

#### Lithium Ion Battery Applications Power Management Switch Applications

- Small footprint due to small and thin package
- Low drain-source ON-resistance:  $R_{DS}$  (ON) = 7.5 m $\Omega$  (typ.)
- Low leakage current:  $I_{DSS} = -10 \ \mu A \ (max) \ (V_{DS} = -30 \ V)$
- Enhancement mode:  $V_{th} = -0.8$  to -2.0 V ( $V_{DS} = -10$  V,  $I_D = -0.5$ mA)

Character	istics	Symbol	Rating	Unit	
Drain-source voltage		V <sub>DSS</sub>	-30	V	
Drain-gate voltage (R	<sub>GS</sub> = 20 kΩ)	V <sub>DGR</sub>	-30	V	
Gate-source voltage		V <sub>GSS</sub>	-25/+20	V	
Drain current	DC (Note 1)	Ι <sub>D</sub>	-11	А	
Drain current	Pulse (Note 1)	I <sub>DP</sub>	-44	~	
Drain power dissipation	on (t = 10 s) (Note 2a)	PD	1.9	W	
Drain power dissipation	on (t = 10 s) (Note 2b)	PD	1.0	W	
Single pulse avalanch	ne energy (Note 3)	E <sub>AS</sub>	79	mJ	
Avalanche current	(Note 1)	I <sub>AR</sub>	-11	А	
Channel temperature		T <sub>ch</sub>	150	°C	
Storage temperature	range	T <sub>stg</sub>	–55 to 150	°C	

#### Absolute Maximum Ratings (Ta = 25°C)

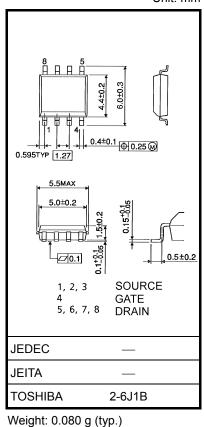
Note 1, Note 2, Note 3 : See the next page.

Using continuously under heavy loads (e.g. the application of high temperature/current/voltage and the significant change in temperature, etc.) may cause this product to decrease in the reliability significantly even if the operating conditions (i.e. operating

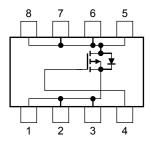
temperature/current/voltage, etc.) are within the absolute maximum ratings.

Please design the appropriate reliability upon reviewing the Toshiba Semiconductor Reliability Handbook ("Handling Precautions"/"Derating Concept and Methods") and individual reliability data (i.e. reliability test report and estimated failure rate, etc).

This transistor is an electrostatic-sensitive device. Handle with care.



## **Circuit Configuration**



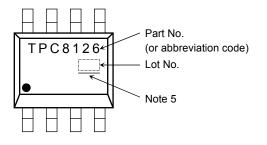
Unit: mm

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## Thermal Characteristics

Characteristics	Symbol	Max	Unit
Thermal resistance, channel to ambient (t = 10 s) (Note 2a)	R <sub>th (ch-a)</sub>	65.8	°C/W
Thermal resistance, channel to ambient (t = 10 s) (Note 2b)	R <sub>th (ch-a)</sub>	125	°C/W

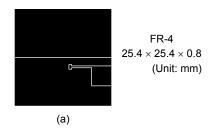
## Marking (Note 4)

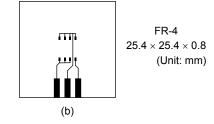


Note 1: Ensure that the channel temperature does not exceed 150  $^{\circ}\text{C}.$ 

Note 2: (a)Device mounted on a glass-epoxy board (a)

(b)Device mounted on a glass-epoxy board (b)





Note 3:  $V_{DD} = -24$  V,  $T_{ch} = 25$  °C (initial), L = 500  $\mu$ H, R<sub>G</sub> = 25  $\Omega$ , I<sub>AR</sub> = -11 A



Week of manufacture (01 for the first week of a year: sequential number up to 52 or 53) Year of manufacture (The last digit of a year)

Note 5: A line under a Lot No. identifies the indication of product Labels. Not underlined: [[Pb]]/INCLUDES > MCV Underlined: [[G]]/RoHS COMPATIBLE or [[G]]/RoHS [[Pb]]

Please contact your TOSHIBA sales representative for details as to environmental matters such as the RoHS compatibility of Product. The RoHS is the Directive 2002/95/EC of the European Parliament and of the Council of 27 January 2003 on the restriction of the use of certain hazardous substances in electrical and electronic equipment.

Electrical Characteristics (Ta = 25°C)

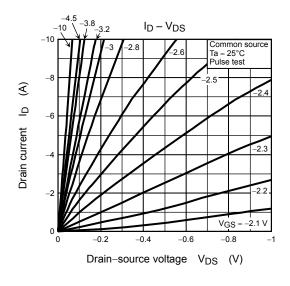
Characteristics		Symbol	Test Condition	Min	Тур.	Max	Unit
Gate leakage curre	ent	I <sub>GSS</sub>	$V_{GS}=\pm 20~V,~V_{DS}=0~V$	_		±100	nA
Drain cut-OFF curr	rent	I <sub>DSS</sub>	$V_{DS} = -30$ V, $V_{GS} = 0$ V	_	_	-10	μA
Drain-source breal	kdown voltago	V (BR) DSS	$I_D = -10$ mA, $V_{GS} = 0$ V	-30		_	v
Drain-source breat	Kuowii vollage	V (BR) DSX	$I_D = -10 \text{ mA}, V_{GS} = 10 \text{ V}$ (Note 6)	-21	_	_	v
Gate threshold voltage		V <sub>th</sub>	$V_{DS} = -10 \text{ V}, \text{ I}_{D} = -0.5 \text{ mA}$	-0.8		-2.0	V
Drain-source ON-resistance		Pro (ou)	$V_{GS}$ = –4.5 V, $I_D$ = –5.5 A	_	10.5	14	mΩ
		RDS (ON)	$V_{GS} = -10 \text{ V}, \text{ I}_{D} = -5.5 \text{ A}$	_	7.5	10	
Input capacitance		C <sub>iss</sub>	V <sub>DS</sub> = -10 V, V <sub>GS</sub> = 0 V, f = 1 MHz	_	2400	_	pF
Reverse transfer capacitance		C <sub>rss</sub>		_	400	_	
Output capacitance		C <sub>oss</sub>		_	460	_	
V (BR) DSXID = -10 mA, VGS = 10 V(Note 6)-21Gate threshold voltageVthVDS = -10 V, ID = -0.5 mA-0.8Drain-source ON-resistanceRDS (ON)VGS = -4.5 V, ID = -5.5 A1Input capacitanceCissVDS = -10 V, ID = -5.5 A1Input capacitanceCissVDS = -10 V, VGS = 0 V, f = 1 MHz2Output capacitanceCossVDS = -10 V, VGS = 0 V, f = 1 MHz2Output capacitanceCoss2Turn-ON timetrVGS -10 V2Fall timetrVOS -10 VTurn-OFF timetoffDuty ≤ 1%, tw = 10 µs2Total gate charge (gate-source plus gate-drain)QgVDS ~ -24 V, VGS = -10 V,2	Rise time	tr	$V_{CS} = \frac{0}{10} V_{CS} = -5.5 A$	—	8		
	16		ns				
	Fall time	t <sub>f</sub>	لَّنْ أَسْ الْمَانَةُ اللَّهُ اللَّٰٰ MDD ≈ −15 V	—	65		115
	Turn-OFF time	t <sub>off</sub>		_	200		
			Vpp≈-24 V Vcs=-10 V		56		nC
Gate-source charge 1		Q <sub>gs1</sub>	$I_{\rm D} = -11  {\rm A}$	—	5.6	_	
Gate-drain ("miller	") charge	Q <sub>gd</sub>			15		

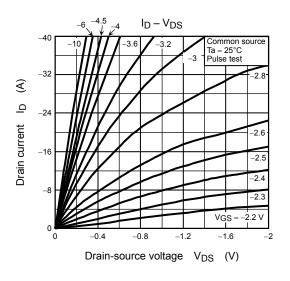
### Source-Drain Ratings and Characteristics (Ta = 25°C)

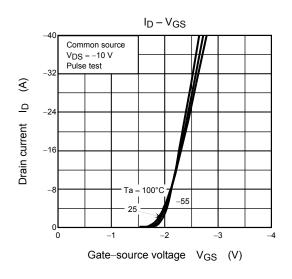
Characteristics		Symbol	Test Condition	Min	Тур.	Max	Unit	
Drain reverse current	Pulse	(Note 1)	I <sub>DRP</sub>	—	_	_	-44	А
Forward voltage (dio	de)		V <sub>DSF</sub>	I <sub>DR</sub> = -11 A, V <sub>GS</sub> = 0 V		_	1.2	V

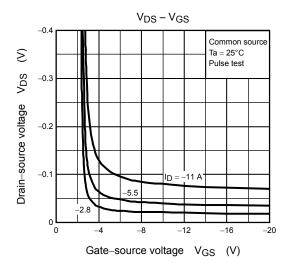
Note 6: VDSX mode (the application of a plus voltage between gate and source) may cause decrease in maximum rating of drain-source voltage.

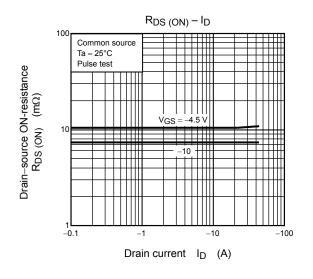
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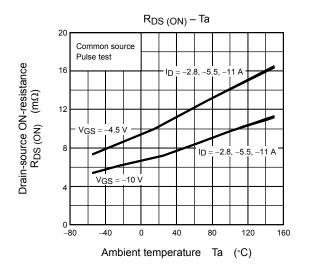


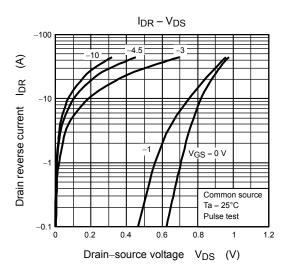


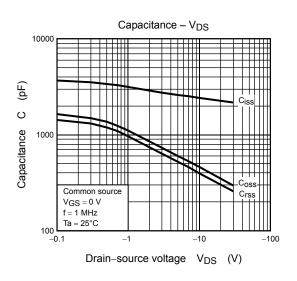


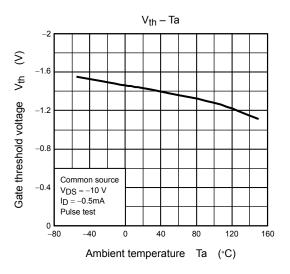


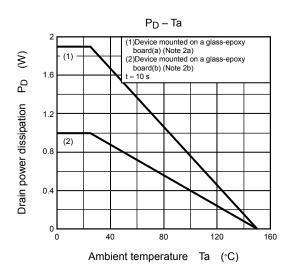
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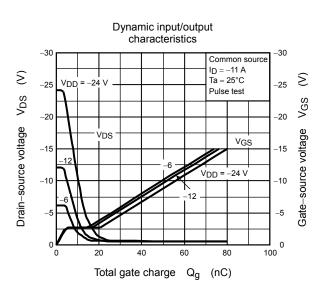


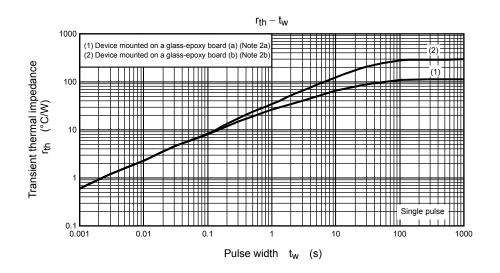


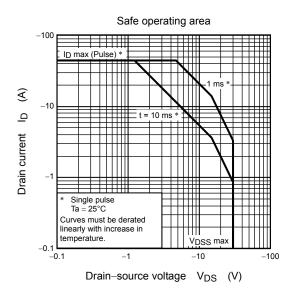












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